PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031
S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Pa	perwork Reduction Act	of 1995,			ion unless it contains a valid OMB control number.	
Substitut	e for form 1449A/PTO		1	Complete if Known		
INFO	DMATION I	חופר	Aditso	Application Number	08/818,884	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Filing Date	March 17, 1997	
SIA				First Named Inventor	Shunpei YAMAZAKI et al.	
	(use as many sheets	as necess	ary)	Group Art Unit	2871	
				Examiner Name	D. Nguyen	
Sheet	1	of	ı	Attorney Docket Number	0756-1653	

MAR 9 1 2006

U.S. PATENT DOCUMENTS							
Examiner Initials*	Cite No.'	U.S. Patent Document		Name of Patentee or Applicant of Cited	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
		Number	Kind Code ² (If known)	Document	MM-DD-YYYY		
8 ~		5,616,944		Mizutani et al.	04/01/1997		
D7~		5,851,440		Tanaka et al.	12/22/1998	-	
pr		4,743,567		Pandya et al.	05/10/1988	_	
DU		5,514,879		Yamazaki	05/07/1996		
		ļ					
	ļ			· .			
	<u> </u>						
			_				
	<u> </u>	1					

					FOREIGN	PATENT DOC	UMENTS		
Examiner Initials	Cite No.'	Foreign Patent Document				Name of Patentee or	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant	
		Office'	Number*	Kind Code ² (if known)	Applica	Applicant of Cited Document	MM-DD-YYYY	Passages or Relevant Figures Appear	T*
									··········
· · · · · · ·			0	THER PRI	OR ART – N	ON PATENT LITE	RATURE DOCUMENTS		
Examiner Initials*	Cite No. I	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.							
DN		Crys	M.K. HATALIS et al., High-Performance Thin-Film Transistors in Low-Temperature Crystallized LPCVD Amorphous Silicon Films, IEEE Electron Device Letters. Vol. 1, EDL8, No. 8, August, 1987, Pages 361-364.						
		1							\dashv

- 1					
	Examiner	A . f	Date	d in l	
		$O_{\mathcal{A}}((A)\cup\mathcal{C}_{\mathcal{A}})$	Date	\.~!!D!#f	
	Signature	01000 9140	Considered	83 / 88 / 0 h	
	O'BRUTO!				

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

¹ Unique citation designation number. ² Applicant is to place a check mark here if English language Translation is attached.